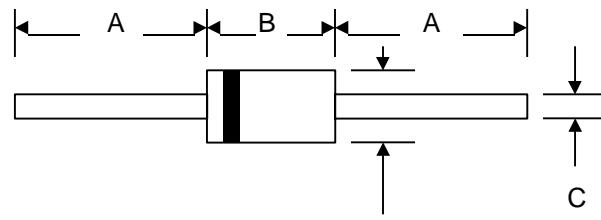


3.0A SILICON RECTIFIER

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability



Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Epoxy: UL 94V-O rate flame retardant

DO-201AD		
Dim	Min	Max
A	25.4	—
B	8.50	9.50
C	1.20	1.30
D	5.0	5.60

All Dimensions in mm

Maximum Ratings and Electrical Characteristics $\text{@T}_A=25^\circ\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Characteristic	Symbol	1N 5400	1N 5401	1N 5402	1N 5404	1N 5406	1N 5407	1N 5408	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) $\text{@T}_A = 75^\circ\text{C}$	I _o				3.0				A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}				200				A
Forward Voltage $\text{@I}_F = 3.0\text{A}$	V _{FM}				1.0				V
Peak Reverse Current $\text{@T}_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage $\text{@T}_A = 100^\circ\text{C}$	I _{RM}				5.0 100				μA
Typical Junction Capacitance (Note 2)	C _j				50				pF
Typical Thermal Resistance Junction to Ambient (Note 1)	R _{θJA}				18				K/W
Operating Temperature Range	T _j				-65 to +125				$^\circ\text{C}$
Storage Temperature Range	T _{STG}				-65 to +150				$^\circ\text{C}$

*Glass passivated forms are available upon request

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

3.0A SILICON RECTIFIER
Typical Characteristics
